

**INFORMATION DISCLOSURE
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ATTY. DOCKET NO.

160-410

CONTINUATION OF SERIAL NO.

10/229,067

APPLICANT

Nakamura et al

(Use several sheets if necessary)

FILING DATE

March 16, 2004

GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	4,862,471	8/1989	Pankove	372	45	
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		Narukawa et al Appl. Phys. Lett. 70 (8), pp 981-983, 2/1997 Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm
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